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What is "Embedded - Microcontrollers"?

"Embedded - Microcontrollers" refer to small, integrated circuits designed to perform specific tasks within larger systems. These microcontrollers are essentially compact computers on a single chip, containing a processor core, memory, and programmable input/output peripherals. They are called "embedded" because they are embedded within electronic devices to control various functions, rather than serving as standalone computers. Microcontrollers are crucial in modern electronics, providing the intelligence and control needed for a wide range of applications.

Applications of "<u>Embedded - Microcontrollers</u>"

Details	
Product Status	Obsolete
Core Processor	RL78
Core Size	16-Bit
Speed	32MHz
Connectivity	CSI, I ² C, LINbus, UART/USART
Peripherals	DMA, LVD, POR, PWM, WDT
Number of I/O	82
Program Memory Size	128KB (128K x 8)
Program Memory Type	FLASH
EEPROM Size	8K x 8
RAM Size	12K x 8
Voltage - Supply (Vcc/Vdd)	2.4V ~ 5.5V
Data Converters	A/D 20x8/10b
Oscillator Type	Internal
Operating Temperature	-40°C ~ 85°C (TA)
Mounting Type	Surface Mount
Package / Case	100-LQFP
Supplier Device Package	100-LQFP (14x14)
Purchase URL	https://www.e-xfl.com/product-detail/renesas-electronics-america/r5f100pggfb-v0

Email: info@E-XFL.COM

Address: Room A, 16/F, Full Win Commercial Centre, 573 Nathan Road, Mongkok, Hong Kong

Table 1-1. List of Ordering Part Numbers

(4/12)

Pin count	Package	Data flash	Fields of Application	Ordering Part Number
44 pins	44-pin plastic LQFP (10 × 10 mm, 0.8 mm	Mounted	А	R5F100FAAFP#V0, R5F100FCAFP#V0, R5F100FDAFP#V0, R5F100FEAFP#V0, R5F100FFAFP#V0, R5F100FGAFP#V0,
	pitch)			R5F100FHAFP#V0, R5F100FJAFP#V0, R5F100FKAFP#V0,
	,			R5F100FLAFP#V0
				R5F100FAAFP#X0, R5F100FCAFP#X0, R5F100FDAFP#X0,
				R5F100FEAFP#X0, R5F100FFAFP#X0, R5F100FGAFP#X0,
				R5F100FHAFP#X0, R5F100FJAFP#X0, R5F100FKAFP#X0,
				R5F100FLAFP#X0
			D	R5F100FADFP#V0, R5F100FCDFP#V0, R5F100FDDFP#V0,
				R5F100FEDFP#V0, R5F100FFDFP#V0, R5F100FGDFP#V0,
				R5F100FHDFP#V0, R5F100FJDFP#V0, R5F100FKDFP#V0,
				R5F100FLDFP#V0
				R5F100FADFP#X0, R5F100FCDFP#X0, R5F100FDDFP#X0,
				R5F100FEDFP#X0, R5F100FFDFP#X0, R5F100FGDFP#X0,
				R5F100FHDFP#X0, R5F100FJDFP#X0, R5F100FKDFP#X0,
				R5F100FLDFP#X0
			G	R5F100FAGFP#V0, R5F100FCGFP#V0, R5F100FDGFP#V0,
				R5F100FEGFP#V0, R5F100FFGFP#V0, R5F100FGGFP#V0,
				R5F100FHGFP#V0, R5F100FJGFP#V0
				R5F100FAGFP#X0, R5F100FCGFP#X0, R5F100FDGFP#X0,
				R5F100FEGFP#X0, R5F100FFGFP#X0, R5F100FGGFP#X0,
				R5F100FHGFP#X0, R5F100FJGFP#X0
		Not	Α	R5F101FAAFP#V0, R5F101FCAFP#V0, R5F101FDAFP#V0,
		mounted		R5F101FEAFP#V0, R5F101FFAFP#V0, R5F101FGAFP#V0,
				R5F101FHAFP#V0, R5F101FJAFP#V0, R5F101FKAFP#V0,
				R5F101FLAFP#V0
				R5F101FAAFP#X0, R5F101FCAFP#X0, R5F101FDAFP#X0,
				R5F101FEAFP#X0, R5F101FFAFP#X0, R5F101FGAFP#X0,
				R5F101FHAFP#X0, R5F101FJAFP#X0, R5F101FKAFP#X0,
				R5F101FLAFP#X0
			D	R5F101FADFP#V0, R5F101FCDFP#V0, R5F101FDDFP#V0,
				R5F101FEDFP#V0, R5F101FFDFP#V0, R5F101FGDFP#V0,
				R5F101FHDFP#V0, R5F101FJDFP#V0, R5F101FKDFP#V0,
				R5F101FLDFP#V0
				R5F101FADFP#X0, R5F101FCDFP#X0, R5F101FDDFP#X0,
				R5F101FEDFP#X0, R5F101FFDFP#X0, R5F101FGDFP#X0,
				R5F101FHDFP#X0, R5F101FJDFP#X0, R5F101FKDFP#X0,
				R5F101FLDFP#X0

Note For the fields of application, refer to Figure 1-1 Part Number, Memory Size, and Package of RL78/G13.

Caution The ordering part numbers represent the numbers at the time of publication. For the latest ordering part numbers, refer to the target product page of the Renesas Electronics website.



Table 1-1. List of Ordering Part Numbers

(11/12)

Pin count	Package	Data flash	Fields of Application	Ordering Part Number
100 pins	100-pin plastic LFQFP (14 × 14 mm, 0.5 mm pitch)	Mounted	A	R5F100PFAFB#V0, R5F100PGAFB#V0, R5F100PHAFB#V0, R5F100PJAFB#V0, R5F100PKAFB#V0, R5F100PLAFB#V0 R5F100PFAFB#X0, R5F100PGAFB#X0, R5F100PHAFB#X0,
			D	R5F100PJAFB#X0, R5F100PKAFB#X0, R5F100PLAFB#X0 R5F100PFDFB#V0, R5F100PGDFB#V0, R5F100PHDFB#V0, R5F100PJDFB#V0, R5F100PKDFB#V0, R5F100PLDFB#V0
				R5F100PFDFB#X0, R5F100PGDFB#X0, R5F100PHDFB#X0, R5F100PJDFB#X0, R5F100PKDFB#X0, R5F100PLDFB#X0
			G	R5F100PFGFB#V0, R5F100PGGFB#V0, R5F100PHGFB#V0, R5F100PJGFB#V0 R5F100PFGFB#X0, R5F100PGGFB#X0, R5F100PHGFB#X0,
		Not mounted	A	R5F100PJGFB#X0 R5F101PFAFB#V0, R5F101PGAFB#V0, R5F101PHAFB#V0, R5F101PJAFB#V0, R5F101PKAFB#V0, R5F101PLAFB#V0
				R5F101PFAFB#X0, R5F101PGAFB#X0, R5F101PHAFB#X0, R5F101PJAFB#X0, R5F101PKAFB#X0, R5F101PLAFB#X0
			D	R5F101PFDFB#V0, R5F101PGDFB#V0, R5F101PHDFB#V0, R5F101PJDFB#V0, R5F101PKDFB#V0, R5F101PLDFB#V0 R5F101PFDFB#X0, R5F101PFDFB#X0, R5F101PHDFB#X0,
				R5F101PJDFB#X0, R5F101PKDFB#X0, R5F101PLDFB#X0
	100-pin plastic LQFP (14 × 20 mm, 0.65 mm pitch)	Mounted	A	R5F100PFAFA#V0, R5F100PGAFA#V0, R5F100PHAFA#V0, R5F100PJAFA#V0, R5F100PKAFA#V0, R5F100PLAFA#V0 R5F100PFAFA#X0, R5F100PGAFA#X0, R5F100PHAFA#X0,
			D	R5F100PJAFA#X0, R5F100PKAFA#X0, R5F100PLAFA#X0 R5F100PFDFA#V0, R5F100PGDFA#V0, R5F100PHDFA#V0, R5F100PJDFA#V0, R5F100PKDFA#V0, R5F100PLDFA#V0
			G	R5F100PFDFA#X0, R5F100PGDFA#X0, R5F100PHDFA#X0, R5F100PJDFA#X0, R5F100PKDFA#X0, R5F100PLDFA#X0 R5F100PFGFA#V0, R5F100PGGFA#V0, R5F100PHGFA#V0,
			G	R5F100PFGFA#V0, R5F100PGGFA#V0, R5F100PHGFA#V0, R5F100PFGFA#X0, R5F100PGGFA#X0, R5F100PHGFA#X0,
				R5F100PJGFA#X0
		Not	A	R5F101PFAFA#V0, R5F101PGAFA#V0, R5F101PHAFA#V0,
		mounted		R5F101PJAFA#V0, R5F101PKAFA#V0, R5F101PLAFA#V0 R5F101PFAFA#X0, R5F101PGAFA#X0, R5F101PHAFA#X0,
			D	R5F101PJAFA#X0, R5F101PKAFA#X0, R5F101PLAFA#X0 R5F101PFDFA#V0, R5F101PGDFA#V0, R5F101PHDFA#V0,
				R5F101PJDFA#V0, R5F101PKDFA#V0, R5F101PLDFA#V0 R5F101PFDFA#X0, R5F101PGDFA#X0, R5F101PHDFA#X0,
				R5F101PJDFA#X0, R5F101PKDFA#X0, R5F101PLDFA#X0

Note For the fields of application, refer to Figure 1-1 Part Number, Memory Size, and Package of RL78/G13.

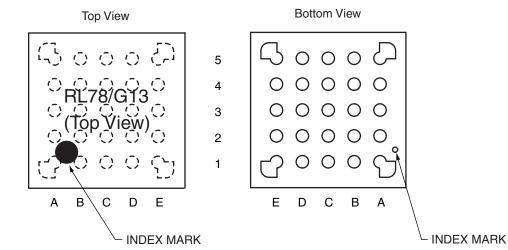
Caution The ordering part numbers represent the numbers at the time of publication. For the latest ordering part numbers, refer to the target product page of the Renesas Electronics website.



1.3.3 25-pin products

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• 25-pin plastic WFLGA (3 × 3 mm, 0.50 mm pitch)

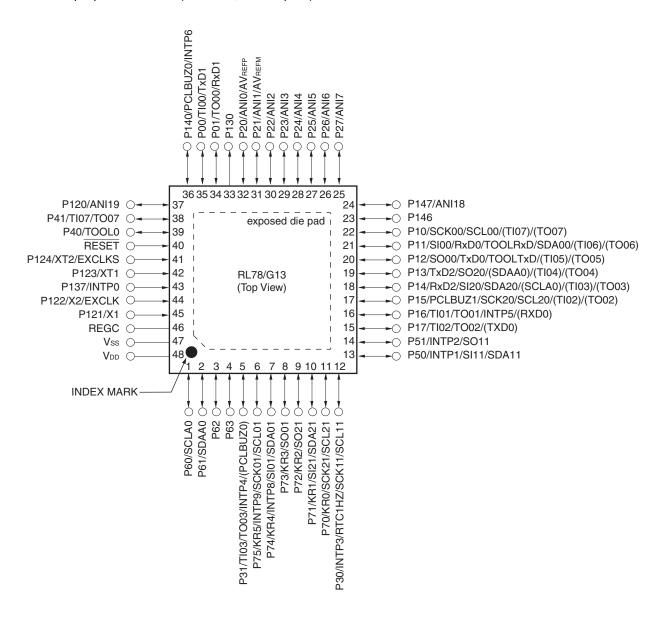


	Α	В	С	D	E	
5	P40/TOOL0	RESET	P01/ANI16/ TO00/RxD1	P22/ANI2	P147/ANI18	5
4	P122/X2/ EXCLK	P137/INTP0	P00/ANI17/ TI00/TxD1	P21/ANI1/ AVREFM	P10/SCK00/ SCL00	4
3	P121/X1	V _{DD}	P20/ANI0/ AV _{REFP}	P12/SO00/ TxD0/ TOOLTxD	P11/SI00/ RxD0/ TOOLRxD/ SDA00	3
2	REGC	Vss	P30/INTP3/ SCK11/SCL11	P17/Tl02/ TO02/SO11	P50/INTP1/ SI11/SDA11	2
1	P60/SCLA0	P61/SDAA0	P31/TI03/ TO03/INTP4/ PCLBUZ0	P16/TI01/ TO01/INTP5	P130	1
	A	В	С	D	Е	

Caution Connect the REGC pin to Vss via a capacitor (0.47 to 1 μ F).

Remark For pin identification, see **1.4 Pin Identification**.

• 48-pin plastic HWQFN (7 × 7 mm, 0.5 mm pitch)



Caution Connect the REGC pin to Vss via a capacitor (0.47 to 1 μ F).

Remarks 1. For pin identification, see 1.4 Pin Identification.

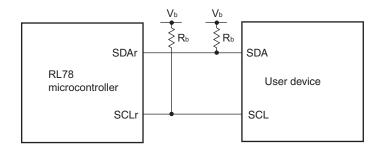
- Functions in parentheses in the above figure can be assigned via settings in the peripheral I/O redirection register (PIOR). Refer to Figure 4-8 Format of Peripheral I/O Redirection Register (PIOR) in the RL78/G13 User's Manual.
- 3. It is recommended to connect an exposed die pad to $V_{\rm ss.}$

 $(T_A = -40 \text{ to } +85^{\circ}\text{C}, 1.6 \text{ V} \le \text{EV}_{DD0} = \text{EV}_{DD1} \le \text{V}_{DD} \le 5.5 \text{ V}, \text{Vss} = \text{EV}_{SS0} = \text{EV}_{SS1} = 0 \text{ V})$ (3/5)

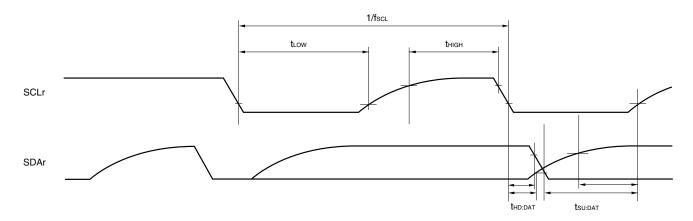
Items	Symbol	Conditions		MIN.	TYP.	MAX.	Unit
Input voltage, high	V _{IH1}	P00 to P07, P10 to P17, P30 to P37, P40 to P47, P50 to P57, P64 to P67, P70 to P77, P80 to P87, P90 to P97, P100 to P106, P110 to P117, P120, P125 to P127, P140 to P147		0.8EVDD0		EV _{DD0}	V
	V _{IH2}	P01, P03, P04, P10, P11, P13 to P17, P43, P44, P53 to P55,	TTL input buffer 4.0 V ≤ EV _{DD0} ≤ 5.5 V	2.2		EV _{DD0}	V
		P80, P81, P142, P143	TTL input buffer $3.3 \text{ V} \le \text{EV}_{\text{DD0}} < 4.0 \text{ V}$	2.0		EV _{DD0}	V
			TTL input buffer 1.6 V ≤ EV _{DD0} < 3.3 V	1.5		EV _{DD0}	V
	V _{IH3}	P20 to P27, P150 to P156		0.7V _{DD}		V _{DD}	٧
	V _{IH4}	P60 to P63		0.7EV _{DD0}		6.0	٧
	V _{IH5}	P121 to P124, P137, EXCLK, EXCL	0.8V _{DD}		V _{DD}	٧	
Input voltage, low	V _{IL1}	P00 to P07, P10 to P17, P30 to P37, P40 to P47, P50 to P57, P64 to P67, P70 to P77, P80 to P87, P90 to P97, P100 to P106, P110 to P117, P120, P125 to P127, P140 to P147	,	0		0.2EV _{DD0}	V
	V _{IL2}	P01, P03, P04, P10, P11, P13 to P17, P43, P44, P53 to P55,	TTL input buffer 4.0 V ≤ EV _{DD0} ≤ 5.5 V	0		0.8	V
		P80, P81, P142, P143	TTL input buffer 3.3 V ≤ EV _{DD0} < 4.0 V	0		0.5	V
			TTL input buffer 1.6 V ≤ EV _{DD0} < 3.3 V	0		0.32	V
	VIL3	P20 to P27, P150 to P156		0		0.3V _{DD}	٧
	V _{IL4}	P60 to P63		0		0.3EV _{DD0}	٧
	V _{IL5}	P121 to P124, P137, EXCLK, EXCL	KS, RESET	0		0.2V _{DD}	٧

Caution The maximum value of V_{IH} of pins P00, P02 to P04, P10 to P15, P17, P43 to P45, P50, P52 to P55, P71, P74, P80 to P82, P96, and P142 to P144 is EV_{DD0}, even in the N-ch open-drain mode.

Simplified I²C mode connection diagram (during communication at different potential)



Simplified I²C mode serial transfer timing (during communication at different potential)



- **Remarks 1.** $R_b[\Omega]$:Communication line (SDAr, SCLr) pull-up resistance, $C_b[F]$: Communication line (SDAr, SCLr) load capacitance, $V_b[V]$: Communication line voltage
 - 2. r: IIC number (r = 00, 01, 10, 20, 30, 31), g: PIM, POM number (g = 0, 1, 4, 5, 8, 14)
 - 3. fmck: Serial array unit operation clock frequency
 (Operation clock to be set by the CKSmn bit of serial mode register mn (SMRmn). m: Unit number,
 n: Channel number (mn = 00, 01, 02, 10, 12, 13)

(2) I2C fast mode

(Ta = -40 to +85°C, 1.6 V \leq EVDD0 = EVDD1 \leq VDD \leq 5.5 V, Vss = EVss0 = EVss1 = 0 V)

Parameter	Symbol	Сог	Conditions H		HS (high-speed main) Mode		LS (low-speed main) Mode		LV (low-voltage main) Mode	
				MIN.	MAX.	MIN.	MAX.	MIN.	MAX.	
SCLA0 clock frequency	fscL	Fast mode:	$2.7~V \le EV_{DD0} \le 5.5~V$	0	400	0	400	0	400	kHz
		fc∟κ≥ 3.5 MHz	1.8 V ≤ EV _{DD0} ≤ 5.5 V	0	400	0	400	0	400	kHz
Setup time of restart	tsu:sta	$2.7 \text{ V} \leq \text{EV}_{\text{DD0}} \leq 5.8$	5 V	0.6		0.6		0.6		μS
condition		$1.8 \text{ V} \leq \text{EV}_{\text{DD0}} \leq 5.8$	5 V	0.6		0.6		0.6		μS
Hold time ^{Note 1}	thd:sta	$2.7 \text{ V} \leq \text{EV}_{\text{DD0}} \leq 5.8$	7 V ≤ EV _{DD0} ≤ 5.5 V			0.6		0.6		μS
		$1.8~V \leq EV_{DD0} \leq 5.5~V$		0.6		0.6		0.6		μS
Hold time when SCLA0 =	tLOW	$2.7 \text{ V} \le \text{EV}_{\text{DD0}} \le 5.5 \text{ V}$		1.3		1.3		1.3		μS
" <u>L</u> "		$1.8 \text{ V} \le \text{EV}_{\text{DD0}} \le 5.5 \text{ V}$		1.3		1.3		1.3		μS
Hold time when SCLA0 =	tніgн	$2.7 \text{ V} \leq \text{EV}_{\text{DD0}} \leq 5.8$	5 V	0.6		0.6		0.6		μS
"H"		1.8 V ≤ EV _{DD0} ≤ 5.8	5 V	0.6		0.6		0.6		μS
Data setup time	tsu:dat	$2.7 \text{ V} \leq \text{EV}_{\text{DD0}} \leq 5.8$	5 V	100		100		100		μS
(reception)		1.8 V ≤ EV _{DD0} ≤ 5.8	5 V	100		100		100		μS
Data hold time	thd:dat	$2.7 \text{ V} \leq \text{EV}_{\text{DD0}} \leq 5.8$	5 V	0	0.9	0	0.9	0	0.9	μS
(transmission)Note 2		$1.8 \text{ V} \leq \text{EV}_{\text{DD0}} \leq 5.8$	5 V	0	0.9	0	0.9	0	0.9	μS
Setup time of stop	tsu:sto	$2.7 \text{ V} \le \text{EV}_{\text{DD0}} \le 5.$	5 V	0.6		0.6		0.6		μS
condition		$1.8 \text{ V} \le \text{EV}_{\text{DD0}} \le 5.8$	5 V	0.6		0.6		0.6		μS
Bus-free time	t BUF	$2.7 \text{ V} \leq \text{EV}_{\text{DD0}} \leq 5.8$	5 V	1.3		1.3		1.3		μS
		$1.8 \text{ V} \le \text{EV}_{\text{DD0}} \le 5.8$	5 V	1.3		1.3		1.3		μS

Notes 1. The first clock pulse is generated after this period when the start/restart condition is detected.

2. The maximum value (MAX.) of thd:DAT is during normal transfer and a wait state is inserted in the ACK (acknowledge) timing.

Caution The values in the above table are applied even when bit 2 (PIOR2) in the peripheral I/O redirection register (PIOR) is 1. At this time, the pin characteristics (IoH1, IoL1, VOH1, VOL1) must satisfy the values in the redirect destination.

Remark The maximum value of Cb (communication line capacitance) and the value of Rb (communication line pull-up resistor) at that time in each mode are as follows.

Fast mode: $C_b = 320 \text{ pF}, R_b = 1.1 \text{ k}\Omega$

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3.3 DC Characteristics

3.3.1 Pin characteristics

 $(T_A = -40 \text{ to } +105^{\circ}\text{C}, 2.4 \text{ V} \le \text{EV}_{DD0} = \text{EV}_{DD1} \le \text{V}_{DD} \le 5.5 \text{ V}, \text{Vss} = \text{EV}_{SS0} = \text{EV}_{SS1} = 0 \text{ V}) (1/5)$

Items	Symbol	Conditions		MIN.	TYP.	MAX.	Unit
Output current, high ^{Note 1}	Іон1	Per pin for P00 to P07, P10 to P17, P30 to P37, P40 to P47, P50 to P57, P64 to P67, P70 to P77, P80 to P87, P90 to P97, P100 to P106, P110 to P117, P120, P125 to P127, P130, P140 to P147	$2.4~V \le EV_{DD0} \le 5.5~V$			-3.0 Note 2	mA
		Total of P00 to P04, P07, P32 to P37,	$4.0~V \leq EV_{DD0} \leq 5.5~V$			-30.0	mA
		P125 to P127, P130, P140 to P145	$2.7~V \leq EV_{DD0} < 4.0~V$			-10.0	mA
		(When duty $\leq 70\%^{\text{Note 3}}$)	$2.4~V \le EV_{DD0} < 2.7~V$			-5.0	mA
		Total of P05, P06, P10 to P17, P30, P31,				-30.0	mA
		P50 to P57, P64 to P67, P70 to P77, P80	$2.7~V \leq EV_{DD0} < 4.0~V$			-19.0	mA
		to P87, P90 to P97, P100, P101, P110 to P117, P146, P147 (When duty ≤ 70% Note 3)	$2.4 \text{ V} \le \text{EVddo} < 2.7 \text{ V}$			-10.0	mA
		Total of all pins (When duty $\leq 70\%^{\text{Note 3}}$)	$2.4~V \leq EV_{DD0} \leq 5.5~V$			-60.0	mA
	І он2	Per pin for P20 to P27, P150 to P156	$2,4~V \leq V_{DD} \leq 5.5~V$			-0.1 Note 2	mA
		Total of all pins (When duty ≤ 70% ^{Note 3})	$2.4~V \leq V_{DD} \leq 5.5~V$			-1.5	mA

- **Notes 1**. Value of current at which the device operation is guaranteed even if the current flows from the EV_{DD0}, EV_{DD1}, V_{DD} pins to an output pin.
 - 2. Do not exceed the total current value.
 - **3.** Specification under conditions where the duty factor $\leq 70\%$.

The output current value that has changed to the duty factor > 70% the duty ratio can be calculated with the following expression (when changing the duty factor from 70% to n%).

• Total output current of pins = $(IOH \times 0.7)/(n \times 0.01)$

<Example> Where n = 80% and $I_{OH} = -10.0$ mA

Total output current of pins = $(-10.0 \times 0.7)/(80 \times 0.01) \cong -8.7$ mA

However, the current that is allowed to flow into one pin does not vary depending on the duty factor. A current higher than the absolute maximum rating must not flow into one pin.

Caution P00, P02 to P04, P10 to P15, P17, P43 to P45, P50, P52 to P55, P71, P74, P80 to P82, P96, and P142 to P144 do not output high level in N-ch open-drain mode.

 $(T_A = -40 \text{ to } +105^{\circ}\text{C}, 2.4 \text{ V} \le \text{EV}_{DD0} = \text{EV}_{DD1} \le \text{V}_{DD} \le 5.5 \text{ V}, \text{Vss} = \text{EV}_{SS0} = \text{EV}_{SS1} = 0 \text{ V}) (2/5)$

Items	Symbol	Conditions		MIN.	TYP.	MAX.	Unit
Output current, low ^{Note 1}	lo _{L1}	Per pin for P00 to P07, P10 to P17, P30 to P37, P40 to P47, P50 to P57, P64 to P67, P70 to P77, P80 to P87, P90 to P97, P100 to P106, P110 to P117, P120, P125 to P127, P130, P140 to P147				8.5 Note 2	mA
		Per pin for P60 to P63				15.0 Note 2	mA
		Total of P00 to P04, P07, P32 to	$4.0~V \leq EV_{DD0} \leq 5.5~V$			40.0	mA
		P37, P40 to P47, P102 to P106, P120,	$2.7~V \leq EV_{DD0} < 4.0~V$			15.0	mA
			$2.4~\text{V} \leq \text{EV}_{\text{DD0}} < 2.7~\text{V}$			9.0	mA
		P31, P50 to P57, P60 to P67, P70 to P77, P80 to P87, P90 to P97,	$4.0~V \leq EV_{DD0} \leq 5.5~V$			40.0	mA
			$2.7~V \leq EV_{DD0} < 4.0~V$			35.0	mA
			$2,4 \text{ V} \le \text{EV}_{\text{DD0}} < 2.7 \text{ V}$			20.0	mA
		Total of all pins (When duty ≤ 70% Note 3)				80.0	mA
	lo _{L2}	Per pin for P20 to P27, P150 to P156			_	0.4 Note 2	mA
		Total of all pins (When duty ≤ 70% Note 3)	$2.4~V \leq V_{DD} \leq 5.5~V$			5.0	mA

- **Notes 1**. Value of current at which the device operation is guaranteed even if the current flows from an output pin to the EVsso, EVss1 and Vss pin.
 - 2. Do not exceed the total current value.
 - **3.** Specification under conditions where the duty factor $\leq 70\%$.

The output current value that has changed to the duty factor > 70% the duty ratio can be calculated with the following expression (when changing the duty factor from 70% to n%).

• Total output current of pins = $(lol \times 0.7)/(n \times 0.01)$

<Example> Where n = 80% and IoL = 10.0 mA

Total output current of pins = $(10.0 \times 0.7)/(80 \times 0.01) \approx 8.7 \text{ mA}$

However, the current that is allowed to flow into one pin does not vary depending on the duty factor. A current higher than the absolute maximum rating must not flow into one pin.

 $(T_A = -40 \text{ to } +105^{\circ}\text{C}, 2.4 \text{ V} \le \text{EV}_{DD0} = \text{EV}_{DD1} \le \text{V}_{DD} \le 5.5 \text{ V}, \text{Vss} = \text{EV}_{SS0} = \text{EV}_{SS1} = 0 \text{ V}) (5/5)$

Items	Symbol	Condition	ons		MIN.	TYP.	MAX.	Unit
Input leakage current, high	Ішні	P00 to P07, P10 to P17, P30 to P37, P40 to P47, P50 to P57, P60 to P67, P70 to P77, P80 to P87, P90 to P97, P100 to P106, P110 to P117, P120, P125 to P127, P140 to P147	VI = EVDDO				1	μΑ
	ILIH2	P20 to P27, P1 <u>37,</u> P150 to P156, RESET	VI = VDD				1	μΑ
	Ішнз	P121 to P124 (X1, X2, XT1, XT2, EXCLK, EXCLKS)		In input port or external clock input			1	μΑ
				In resonator connection			10	μΑ
Input leakage current, low	Iuu1	P00 to P07, P10 to P17, P30 to P37, P40 to P47, P50 to P57, P60 to P67, P70 to P77, P80 to P87, P90 to P97, P100 to P106, P110 to P117, P120, P125 to P127, P140 to P147	V _I = EVsso				-1	μΑ
	ILIL2	P20 to P27, P137, P150 to P156, RESET	Vı = Vss				-1	μΑ
	Ішз	P121 to P124 (X1, X2, XT1, XT2, EXCLK, EXCLKS)	Vı = Vss	In input port or external clock input			-1	μΑ
				In resonator connection			-10	μΑ
On-chip pll-up resistance	Rυ	P00 to P07, P10 to P17, P30 to P37, P40 to P47, P50 to P57, P64 to P67, P70 to P77, P80 to P87, P90 to P97, P100 to P106, P110 to P117, P120, P125 to P127, P140 to P147	Vı = EVsso	, In input port	10	20	100	kΩ

3.3.2 Supply current characteristics

(1) Flash ROM: 16 to 64 KB of 20- to 64-pin products (Ta = -40 to +105°C, 2.4 V \leq EVDD0 \leq VDD \leq 5.5 V, Vss = EVss0 = 0 V) (1/2)

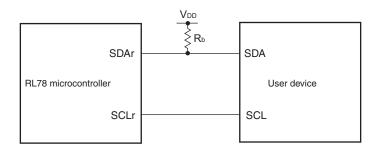
Parameter	Symbol		Conditions					TYP.	MAX.	Unit
Supply current	I _{DD1}	Operating mode	HS (high- speed main)	fih = 32 MHz ^{Note 3}	Basic operatio	V _{DD} = 5.0 V		2.1		mA
Note 1		mode	mode Note 5		n	V _{DD} = 3.0 V		2.1		mA
					Normal	V _{DD} = 5.0 V		4.6	7.5	mA
					operatio n	V _{DD} = 3.0 V		4.6	7.5	mA
				fin = 24 MHz Note 3	Normal	V _{DD} = 5.0 V		3.7	5.8	mA
					operatio n	V _{DD} = 3.0 V		3.7	5.8	mA
				fih = 16 MHz ^{Note 3}	Normal	V _{DD} = 5.0 V		2.7	4.2	mA
					operatio n	V _{DD} = 3.0 V		2.7	4.2	mA
			HS (high-	$f_{MX} = 20 \text{ MHz}^{\text{Note 2}},$	Normal	Square wave input		3.0	4.9	mA
			speed main) mode Note 5	$V_{DD} = 5.0 \text{ V}$	operatio n	Resonator connection		3.2	5.0	mA
				$f_{MX} = 20 \text{ MHz}^{\text{Note 2}},$	Normal	Square wave input		3.0	4.9	mA
			n	operatio n	Resonator connection		3.2	5.0	mA	
			$f_{MX} = 10 \text{ MHz}^{Note 2},$	Normal	Square wave input		1.9	2.9	mA	
			$V_{DD} = 5.0 \text{ V}$	operatio n	Resonator connection		1.9	2.9	mA	
			$f_{MX} = 10 \text{ MHz}^{\text{Note 2}},$ $V_{DD} = 3.0 \text{ V}$	$f_{MX} = 10 \text{ MHz}^{\text{Note 2}},$	Normal	Square wave input		1.9	2.9	mA
				operatio n	Resonator connection		1.9	2.9	mA	
			Subsystem	fsuв = 32.768 kHz	Normal	Square wave input		4.1	4.9	μΑ
			clock operation	Note 4 $T_A = -40^{\circ}C$	operatio n	Resonator connection		4.2	5.0	μΑ
				fsub = 32.768 kHz	Normal	Square wave input		4.1	4.9	μΑ
				T _A = +25°C	operatio n	Resonator connection		4.2	5.0	μΑ
				fsuв = 32.768 kHz	Normal	Square wave input		4.2	5.5	μΑ
				Note 4 $T_A = +50^{\circ}C$	operatio n	Resonator connection		4.3	5.6	μΑ
				fsuв = 32.768 kHz	Normal	Square wave input		4.3	6.3	μΑ
				Note 4 $T_A = +70^{\circ}C$	operatio n	Resonator connection		4.4	6.4	μА
				fsuB = 32.768 kHz	Normal	Square wave input		4.6	7.7	μΑ
			Note 4 T _A − +85°C	operation	Resonator connection		4.7	7.8	μА	
			T _A = +85°C f _{SUB} = 32.768 kHz	Normal	Square wave input		6.9	19.7	μΑ	
				Note 4 $T_A = +105^{\circ}C$	operation	Resonator connection		7.0	19.8	μΑ

(Notes and Remarks are listed on the next page.)

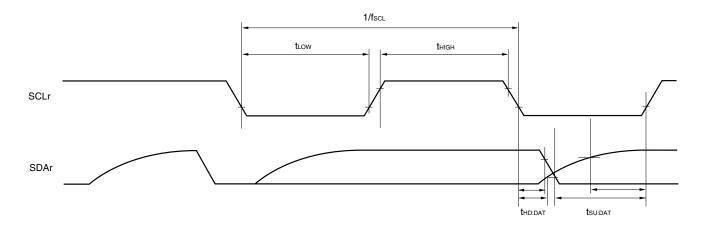
- **6.** Current flowing only to the A/D converter. The supply current of the RL78 microcontrollers is the sum of IDD1 or IDD2 and IADC when the A/D converter is in operation.
- 7. Current flowing only to the LVD circuit. The supply current of the RL78 microcontrollers is the sum of IDD1, IDD2 or IDD3 and ILVD when the LVD circuit is in operation.
- 8. Current flowing only during data flash rewrite.
- **9.** Current flowing only during self programming.
- 10. For shift time to the SNOOZE mode, see 18.3.3 SNOOZE mode in the RL78/G13 User's Manual.
- Remarks 1. fil: Low-speed on-chip oscillator clock frequency
 - 2. fsub: Subsystem clock frequency (XT1 clock oscillation frequency)
 - 3. fclk: CPU/peripheral hardware clock frequency
 - **4.** Temperature condition of the TYP. value is $T_A = 25^{\circ}C$



Simplified I²C mode mode connection diagram (during communication at same potential)



Simplified I²C mode serial transfer timing (during communication at same potential)



Remarks 1. $R_b[\Omega]$:Communication line (SDAr) pull-up resistance, $C_b[F]$: Communication line (SDAr, SCLr) load capacitance

- 2. r: IIC number (r = 00, 01, 10, 11, 20, 21, 30, 31), g: PIM number (g = 0, 1, 4, 5, 8, 14), h: POM number (g = 0, 1, 4, 5, 7 to 9, 14)
- 3. fmck: Serial array unit operation clock frequency
 (Operation clock to be set by the CKSmn bit of serial mode register mn (SMRmn). m: Unit number (m = 0, 1), n: Channel number (n = 0 to 3), mn = 00 to 03, 10 to 13)

(5) Communication at different potential (1.8 V, 2.5 V, 3 V) (UART mode) (2/2)

 $(T_A = -40 \text{ to } +105^{\circ}\text{C}, 2.4 \text{ V} \le \text{EV}_{DD0} = \text{EV}_{DD1} \le \text{V}_{DD} \le 5.5 \text{ V}, \text{Vss} = \text{EV}_{SS0} = \text{EV}_{SS1} = 0 \text{ V})$

Parameter	Symbol		Condit	ions	HS (high-spee	ed main) Mode	Unit	
					MIN.	MAX.		
Transfer rate		Transmission	$4.0 \text{ V} \leq \text{EV}_{\text{DD0}} \leq 5.5$			Note 1	bps	
			$2.7 \text{ V} \le \text{V}_{\text{b}} \le 4.0 \text{ V}$	$2.7~V \leq V_b \leq 4.0~V$	Theoretical value of the maximum transfer rate $C_b = 50 \ pF, \ R_b = 1.4 \ k\Omega, \ V_b = 2.7 \ V$		2.6 Note 2	Mbps
			$2.7 \text{ V} \leq \text{EV}_{\text{DD0}} < 4.0$			Note 3	bps	
	V,	$V,$ $2.3~V \leq V_b \leq 2.7~V$	Theoretical value of the maximum transfer rate $C_b = 50 \ pF, \ R_b = 2.7 \ k\Omega, \ V_b = 2.3 \ V$		1.2 Note 4	Mbps		
			2.4 V ≤ EV _{DD0} < 3.3			Note 5	bps	
			$V,$ $1.6~V \leq V_b \leq 2.0~V$	Theoretical value of the maximum transfer rate $C_b = 50 \text{ pF}, R_b = 5.5 \text{ k}\Omega, V_b = 1.6 V$		0.43 Note 6	Mbps	

Notes 1. The smaller maximum transfer rate derived by using fmck/12 or the following expression is the valid maximum transfer rate.

Expression for calculating the transfer rate when 4.0 V \leq EV_{DD0} \leq 5.5 V and 2.7 V \leq V_b \leq 4.0 V

Maximum transfer rate =
$$\frac{1}{\{-C_b \times R_b \times \ln (1 - \frac{2.2}{V_b})\} \times 3}$$
 [bps]

$$\text{Baud rate error (theoretical value)} = \frac{\frac{1}{\text{Transfer rate} \times 2} - \{-C_b \times R_b \times \ln{(1 - \frac{2.2}{V_b})}\}}{\frac{1}{(\text{Transfer rate})} \times \text{Number of transferred bits}} \times 100 \, [\%]$$

- * This value is the theoretical value of the relative difference between the transmission and reception sides.
- 2. This value as an example is calculated when the conditions described in the "Conditions" column are met. Refer to Note 1 above to calculate the maximum transfer rate under conditions of the customer.
- 3. The smaller maximum transfer rate derived by using fmck/12 or the following expression is the valid maximum transfer rate.

Expression for calculating the transfer rate when 2.7 V \leq EV_{DDO} < 4.0 V and 2.4 V \leq V_b \leq 2.7 V

Maximum transfer rate =
$$\frac{1}{\{-C_b \times R_b \times ln (1 - \frac{2.0}{V_b})\} \times 3}$$
 [bps]

$$\text{Baud rate error (theoretical value)} = \frac{\frac{1}{\text{Transfer rate} \times 2} - \{-C_b \times R_b \times \ln{(1 - \frac{2.0}{V_b})}\}}{\frac{1}{(\text{Transfer rate})} \times \text{Number of transferred bits}} \times 100 \, [\%]$$

- * This value is the theoretical value of the relative difference between the transmission and reception sides.
- **4.** This value as an example is calculated when the conditions described in the "Conditions" column are met. Refer to Note 3 above to calculate the maximum transfer rate under conditions of the customer.



5. The smaller maximum transfer rate derived by using fmck/12 or the following expression is the valid maximum transfer rate.

Expression for calculating the transfer rate when 2.4 V \leq EV_{DD0} < 3.3 V and 1.6 V \leq V_b \leq 2.0 V

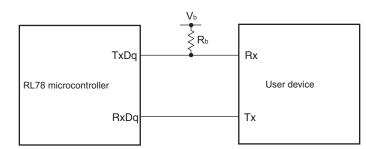
Maximum transfer rate =
$$\frac{1}{\{-C_b \times R_b \times \ln (1 - \frac{1.5}{V_b})\} \times 3}$$
 [bps]

Baud rate error (theoretical value) =
$$\frac{\frac{1}{\text{Transfer rate} \times 2} - \{-C_b \times R_b \times \ln{(1 - \frac{1.5}{V_b})}\}}{(\frac{1}{\text{Transfer rate}}) \times \text{Number of transferred bits}} \times 100 \, [\%]$$

- * This value is the theoretical value of the relative difference between the transmission and reception sides.
- **6.** This value as an example is calculated when the conditions described in the "Conditions" column are met. Refer to Note 5 above to calculate the maximum transfer rate under conditions of the customer.

Caution Select the TTL input buffer for the RxDq pin and the N-ch open drain output (VDD tolerance (for the 20- to 52-pin products)/EVDD tolerance (for the 64- to 100-pin products)) mode for the TxDq pin by using port input mode register g (PIMg) and port output mode register g (POMg). For VIH and VIL, see the DC characteristics with TTL input buffer selected.

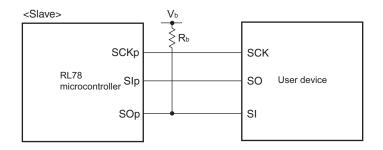
UART mode connection diagram (during communication at different potential)



- Notes 1. Transfer rate in the SNOOZE mode: MAX. 1 Mbps
 - 2. When DAPmn = 0 and CKPmn = 0, or DAPmn = 1 and CKPmn = 1. The SIp setup time becomes "to SCKp↓" when DAPmn = 0 and CKPmn = 1, or DAPmn = 1 and CKPmn = 0.
 - **3.** When DAPmn = 0 and CKPmn = 0, or DAPmn = 1 and CKPmn = 1. The Slp hold time becomes "from SCKp↓" when DAPmn = 0 and CKPmn = 1, or DAPmn = 1 and CKPmn = 0.
 - **4.** When DAPmn = 0 and CKPmn = 0, or DAPmn = 1 and CKPmn = 1. The delay time to SOp output becomes "from SCKp↑" when DAPmn = 0 and CKPmn = 1, or DAPmn = 1 and CKPmn = 0.

Caution Select the TTL input buffer for the SIp pin and SCKp pin and the N-ch open drain output (VDD tolerance (for the 20- to 52-pin products)/EVDD tolerance (for the 64- to 128-pin products)) mode for the SOp pin by using port input mode register g (PIMg) and port output mode register g (POMg). For VH and VIL, see the DC characteristics with TTL input buffer selected.

CSI mode connection diagram (during communication at different potential)



- **Remarks 1.** $R_b[\Omega]$:Communication line (SOp) pull-up resistance, $C_b[F]$: Communication line (SOp) load capacitance, $V_b[V]$: Communication line voltage
 - 2. p: CSI number (p = 00, 01, 10, 20, 30, 31), m: Unit number (m = 0, 1), n: Channel number (n = 00, 01, 02,
 - 10, 12, 13), g: PIM and POM number (g = 0, 1, 4, 5, 8, 14)
 - 3. fmck: Serial array unit operation clock frequency(Operation clock to be set by the CKSmn bit of serial mode register mn (SMRmn).m: Unit number, n: Channel number (mn = 00, 01, 02, 10, 12, 13))
 - **4.** CSI01 of 48-, 52-, 64-pin products, and CSI11 and CSI21 cannot communicate at different potential. Use other CSI for communication at different potential.

(8) Communication at different potential (1.8 V, 2.5 V, 3 V) (simplified I^2C mode) (1/2) (T_A = -40 to +105°C, 2.4 V \leq EV_{DD0} = EV_{DD1} \leq V_{DD} \leq 5.5 V, Vss = EV_{SS0} = EV_{SS1} = 0 V)

Parameter	Symbol	Conditions		speed main) ode	Unit
			MIN.	MAX.	
SCLr clock frequency	fscL	$\begin{aligned} 4.0 \ V &\leq EV_{DD0} \leq 5.5 \ V, \\ 2.7 \ V &\leq V_b \leq 4.0 \ V, \\ C_b &= 50 \ pF, \ R_b = 2.7 \ k\Omega \end{aligned}$		400 Note 1	kHz
		$\begin{aligned} 2.7 \ V &\leq EV_{DD0} < 4.0 \ V, \\ 2.3 \ V &\leq V_b \leq 2.7 \ V, \\ C_b &= 50 \ pF, \ R_b = 2.7 \ k\Omega \end{aligned}$		400 Note 1	kHz
		$ \begin{aligned} &4.0 \; V \leq EV_{DD0} \leq 5.5 \; V, \\ &2.7 \; V \leq V_b \leq 4.0 \; V, \\ &C_b = 100 \; pF, \; R_b = 2.8 \; k\Omega \end{aligned} $		100 Note 1	kHz
		$2.7 \text{ V} \leq \text{EV}_{\text{DDO}} < 4.0 \text{ V},$ $2.3 \text{ V} \leq \text{V}_{\text{b}} \leq 2.7 \text{ V},$ $C_{\text{b}} = 100 \text{ pF}, \text{ R}_{\text{b}} = 2.7 \text{ k}\Omega$		100 Note 1	kHz
		$\begin{aligned} &2.4 \; V \leq EV_{DD0} < 3.3 \; V, \\ &1.6 \; V \leq V_b \leq 2.0 \; V, \\ &C_b = 100 \; pF, \; R_b = 5.5 \; k\Omega \end{aligned}$		100 Note 1	kHz
Hold time when SCLr = "L"	tLOW	$\begin{aligned} 4.0 & \ V \leq EV_{DD0} \leq 5.5 \ V, \\ 2.7 & \ V \leq V_b \leq 4.0 \ V, \\ C_b = 50 \ pF, \ R_b = 2.7 \ k\Omega \end{aligned}$	1200		ns
		$\begin{split} 2.7 \ V & \leq EV_{DD0} < 4.0 \ V, \\ 2.3 \ V & \leq V_b \leq 2.7 \ V, \\ C_b & = 50 \ pF, \ R_b = 2.7 \ k\Omega \end{split}$	1200		ns
		$ \begin{aligned} &4.0 \; V \leq EV_{DD0} \leq 5.5 \; V, \\ &2.7 \; V \leq V_b \leq 4.0 \; V, \\ &C_b = 100 \; pF, \; R_b = 2.8 \; k\Omega \end{aligned} $	4600		ns
		$2.7 \text{ V} \leq \text{EV}_{\text{DD0}} < 4.0 \text{ V},$ $2.3 \text{ V} \leq \text{V}_{\text{b}} \leq 2.7 \text{ V},$ $C_{\text{b}} = 100 \text{ pF}, \text{ R}_{\text{b}} = 2.7 \text{ k}\Omega$	4600		ns
		$2.4 \ V \leq EV_{DD0} < 3.3 \ V,$ $1.6 \ V \leq V_b \leq 2.0 \ V,$ $C_b = 100 \ pF, \ R_b = 5.5 \ k\Omega$	4650		ns
Hold time when SCLr = "H"	tнівн	$\begin{aligned} 4.0 \ V &\leq EV_{DD0} \leq 5.5 \ V, \\ 2.7 \ V &\leq V_b \leq 4.0 \ V, \\ C_b &= 50 \ pF, \ R_b = 2.7 \ k\Omega \end{aligned}$	620		ns
		$2.7 \text{ V} \le \text{EV}_{\text{DD0}} < 4.0 \text{ V},$ $2.3 \text{ V} \le \text{V}_{\text{b}} \le 2.7 \text{ V},$ $C_{\text{b}} = 50 \text{ pF}, \text{ R}_{\text{b}} = 2.7 \text{ k}\Omega$	500		ns
		$\begin{aligned} &4.0 \text{ V} \leq \text{EV}_{\text{DD0}} \leq 5.5 \text{ V}, \\ &2.7 \text{ V} \leq \text{V}_{\text{b}} \leq 4.0 \text{ V}, \\ &C_{\text{b}} = 100 \text{ pF}, \text{ R}_{\text{b}} = 2.8 \text{ k}\Omega \end{aligned}$	2700		ns
		$\begin{aligned} 2.7 & \text{ V} \leq \text{EV}_{\text{DD0}} < 4.0 \text{ V}, \\ 2.3 & \text{ V} \leq \text{V}_{\text{b}} \leq 2.7 \text{ V}, \\ C_{\text{b}} = 100 \text{ pF}, \text{ R}_{\text{b}} = 2.7 \text{ k}\Omega \end{aligned}$	2400		ns
		$2.4 \ V \leq EV_{DD0} < 3.3 \ V,$ $1.6 \ V \leq V_b \leq 2.0 \ V,$ $C_b = 100 \ pF, \ R_b = 5.5 \ k\Omega$	1830		ns

(${f Notes}$ and ${f Caution}$ are listed on the next page, and ${f Remarks}$ are listed on the page after the next page.)

3.6.5 Power supply voltage rising slope characteristics

$(T_A = -40 \text{ to } +105^{\circ}\text{C}, \text{ Vss} = 0 \text{ V})$

Parameter	Symbol	Conditions	MIN.	TYP.	MAX.	Unit
Power supply voltage rising slope	SVDD				54	V/ms

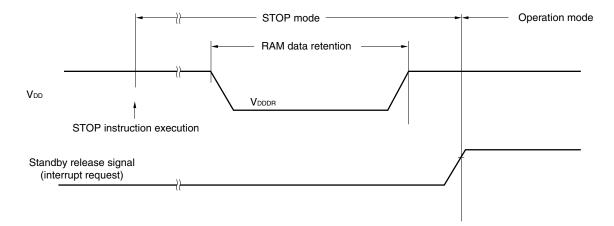
Caution Make sure to keep the internal reset state by the LVD circuit or an external reset until V_{DD} reaches the operating voltage range shown in 3.4 AC Characteristics.

3.7 RAM Data Retention Characteristics

$(T_A = -40 \text{ to } +105^{\circ}\text{C}, \text{ Vss} = 0 \text{ V})$

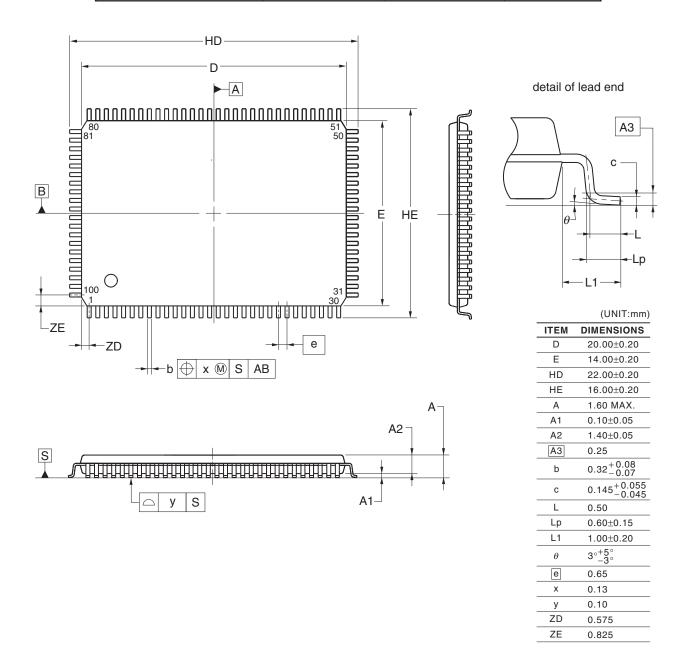
Parameter	Symbol	Conditions	MIN.	TYP.	MAX.	Unit
Data retention supply voltage	V _{DDDR}		1.44 ^{Note}		5.5	٧

Note This depends on the POR detection voltage. For a falling voltage, data in RAM are retained until the voltage reaches the level that triggers a POR reset but not once it reaches the level at which a POR reset is generated.



R5F100PFAFA, R5F100PGAFA, R5F100PHAFA, R5F100PJAFA, R5F100PKAFA, R5F100PLAFA R5F101PFAFA, R5F101PGAFA, R5F101PHAFA, R5F101PJAFA, R5F101PKAFA, R5F101PLAFA R5F100PFDFA, R5F100PGDFA, R5F100PHDFA, R5F100PJDFA, R5F100PKDFA, R5F101PLDFA R5F101PFDFA, R5F101PGDFA, R5F101PHDFA, R5F101PJDFA, R5F101PKDFA, R5F101PLDFA R5F100PFGFA, R5F100PGGFA, R5F100PHGFA, R5F100PJGFA

JEITA Package Code	RENESAS Code	Previous Code	MASS (TYP.) [g]
P-LQFP100-14x20-0.65	PLQP0100JC-A	P100GF-65-GBN-1	0.92



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